NSN 5961-00-554-0267

Thyristor Semiconductor Device - Page 1 of 1

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Inclosure Material:

Ceramic and metal

Overall Length:

Between 0.340 inches and 0.376 inches

Overall Diameter:

Between 0.501 inches and 0.505 inches

Internal Configuration:

Junction contact

Electrode Internally-electrically Connected To Case:

Anode

Mounting Method:

Press fit

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

500.0 forward voltage, peak and 100.0 repetitive peak reverse voltage and 150.0 nonrepetitive peak reverse voltage and 2.0 gate trigger voltage, dc

Current Rating Per Characteristic:

250.00 amperes forward current, average preset and 13.00 amperes forward current, total rms universal and 25.00 amperes forward current, total rms horsepower metric and 40.00 milliamperes forward current, total rms preset

Power Rating Per Characteristic:

5.0 watts small-signal input power, common-collector blank

Maximum Operating Tempurature Per Measurement Point:

100.0 degrees celsius junction

Special Features:

Junction pattern arrangement: pnpn

Terminal Type And Quantity:

3 tab, solder lug and 1 case

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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